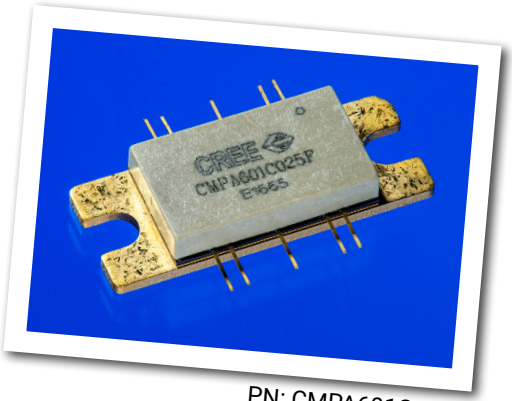
CMPA601C025F

25 W, 6.0 - 12.0 GHz, GaN MMIC, Power Amplifier



PN: CMPA601C025F
Package Type: 440213

The CMPA601C025F is a gallium nitride (GaN) High Electron Mobility Transistor (HEMT) based monolithic microwave integrated circuit (MMIC) on a silicon carbide (SiC) substrate, using a 0.25 µm gate length fabrication process. The semiconductor offers 25 Watts of power from 6 to 12 GHz of instantaneous bandwidth. The GaN HEMT MMIC is housed in a thermally-enhanced, 10-lead 25 mm x 9.9 mm metal/ceramic flanged package. It offers high gain and superior efficiency in a small footprint package at 50 ohms.

Typical Performance Over 6.0-12.0 GHz (T_c = 25°C)

Parameter	6.0 GHz	7.5 GHz	9.0 GHz	10.5 GHz	12.0 GHz	Units
Small Signal Gain	35	34	34	37	31	dB
P_{OUT} @ P_{IN} = 22 dBm	34	51	49	49.5	36.5	W
Power Gain @ P_{IN} = 22 dBm	23	25	25	25	23.5	dB
PAE @ P_{IN} = 22 dBm	21	36	35	33	27	%

Note: All data CW.

Features

- 34 dB Small Signal Gain
- 40 W Typical P_{SAT}
- Operation up to 28 V
- High Breakdown Voltage
- High Temperature Operation
- Size 0.172 x 0.239 x 0.004 inches

Applications

- Jamming Amplifiers
- Test Equipment Amplifiers
- Broadband Amplifiers

Rev 3.0 – May 2017

Absolute Maximum Ratings (not simultaneous) at 25˚C

Parameter	Symbol	Rating	Units	Conditions
Drain-source Voltage	V_{DS}	84	V_{DC}	25˚C
Gate-source Voltage	V_{GS}	-10, +2	V_{DC}	25˚C
Storage Temperature	T_{STG}	-40, +150	˚C	
Operating Junction Temperature	T_J	225	˚C	
Maximum Forward Gate Current	I_{GMAX}	23	mA	25˚C
Soldering Temperature[1]	T_{STG}	245	˚C	
Screw Torque	T	40	in-oz	
Thermal Resistance, Junction to Case[2]	$R_{\theta JC}$	0.85	˚C/W	85˚C @ P_{DISS} = 116 W
Case Operating Temperature[2]	T_C	-40, +150	˚C	

Note[1] Refer to the Application Note on soldering at http://www.cree.com/rf/document-library

Note[2] See also, the Power Dissipation De-rating Curve on page 4

Electrical Characteristics (Frequency = 6.0 GHz to 12.0 GHz unless otherwise stated; T_C = 25˚C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics[1,2]						
Gate Threshold	V_{TH}	-3.8	-2.8	-2.3	V	V_{DS} = 10 V, I_D = 23 mA
Saturated Drain Current	I_{DS}	10.6	13.0	–	A	V_{DS} = 6V, V_{GS} = 2 V
Drain-Source Breakdown Voltage	V_{BD}	84	100	–	V	V_{GS} = -8 V, I_{DS} = 23 mA
RF Characteristics[3]						
Small Signal Gain	S21	28	31	–	dB	V_{DD} = 28 V, I_{DQ} = 2 A, P_{IN} = -30 dBm
Output Power[3,4]	P_{OUT1}	45.5	47.2	–	dBm	V_{DD} = 28 V, I_{DQ} = 2 A, P_{IN} = 22 dBm, Freq = 6 GHz
Output Power[3,4]	P_{OUT2}	45.5	47.1	–	dBm	V_{DD} = 28 V, I_{DQ} = 2 A, P_{IN} = 22 dBm, Freq = 9.5 GHz
Output Power[3,4]	P_{OUT3}	43.7	45.5	–	dBm	V_{DD} = 28 V, I_{DQ} = 2 A, P_{IN} = 22 dBm, Freq = 12 GHz
Power Added Efficiency[3,4]	PAE_1	23	33.2	–	%	V_{DD} = 28 V, I_{DQ} = 2 A, P_{IN} = 22 dBm, Freq = 6 GHz
Power Added Efficiency[3,4]	PAE_2	26	32.3	–	%	V_{DD} = 28 V, I_{DQ} = 2 A, P_{IN} = 22 dBm, Freq = 9.5 GHz
Power Added Efficiency[3,4]	PAE_3	15.5	26.5	–	%	V_{DD} = 28 V, I_{DQ} = 2 A, P_{IN} = 22 dBm, Freq = 12 GHz
Input Return Loss	S11	–	-5	–	dB	V_{DD} = 28 V, I_{DQ} = 2 A, P_{IN} = -30 dBm
Output Return Loss	S22	–	-5	–	dB	V_{DD} = 28 V, I_{DQ} = 2 A, P_{IN} = -30 dBm
Output Mismatch Stress	VSWR	–	5:1	VSWR	Ψ	No damage at all phase angles, V_{DD} = 28 V, I_{DQ} = 2 A, P_{IN} = 22 dBm

Notes:

[1] Measured on-wafer prior to packaging.

[2] Scaled from PCM data.

[3] Measured in CMPA601C025F-AMP with 12.4 GHz low pass filter.

[4] Fixture loss de-embedded using the following offsets. The offset is subtracted from the input offset value and added to the output offset value.

a) 6.0 GHz - 0.13 dB

b) 9.50 GHz - 0.26 dB

c) 12.0 GHz - 0.35 dB

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Figure 1. - Small Signal S-Parameters vs. Frequency
V_{DD} = 28 V, I_{DQ} = 2.0 A, P_{IN} = -30 dBm

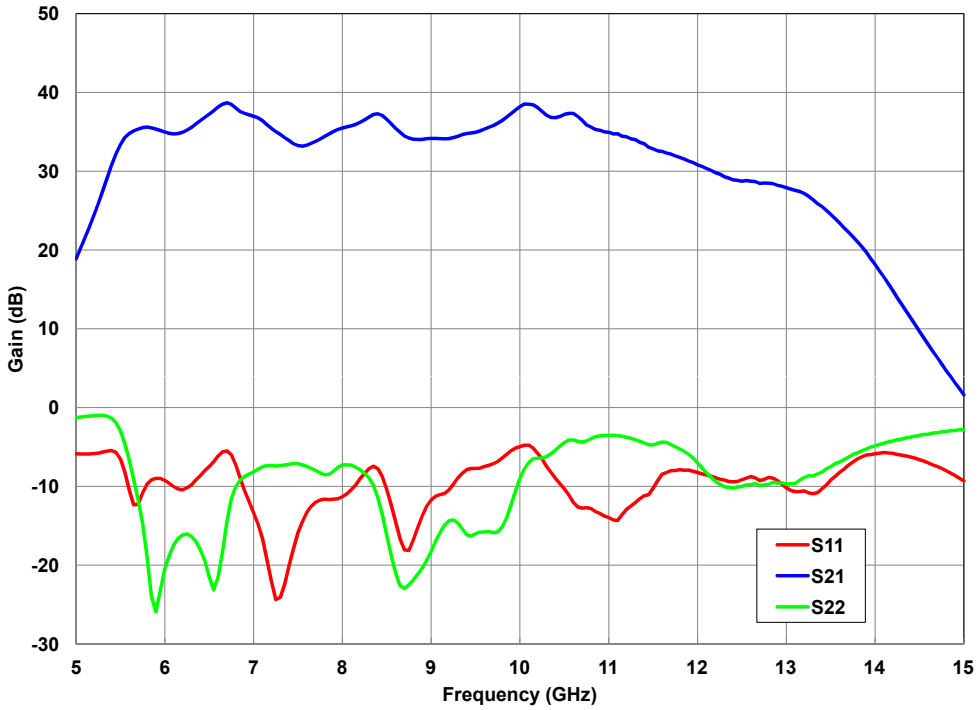

Figure 2. - Output Power, Gain and Power Added Efficiency vs. Input Power
V_{DD} = 28 V, I_{DQ} = 2.0 A, P_{IN} = 22 dBm

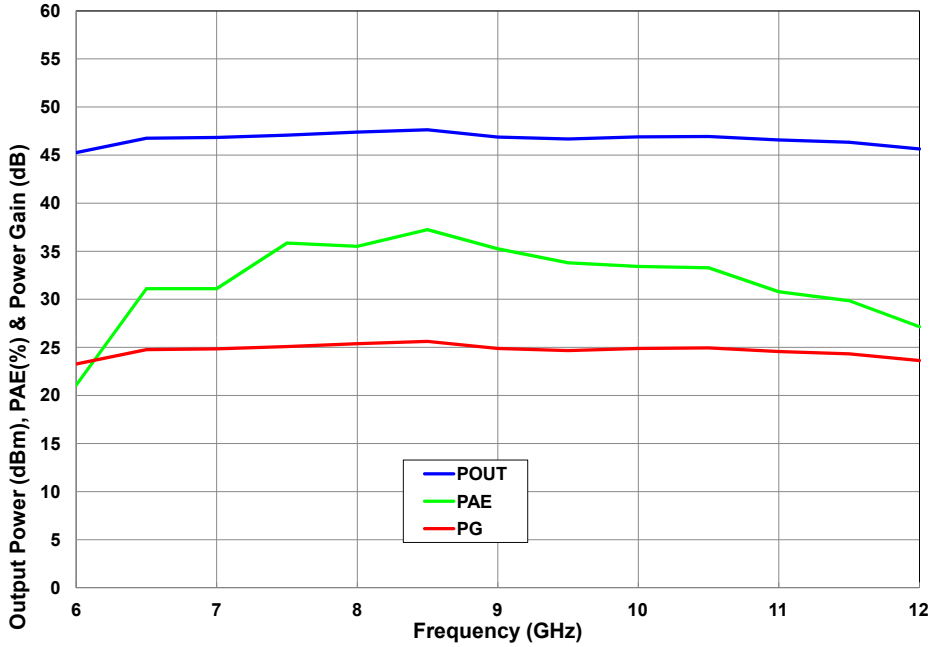

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Figure 3. - Power Added Efficiency vs. Input Power
V_{DD} = 28 V, I_{DQ} = 2.0 A

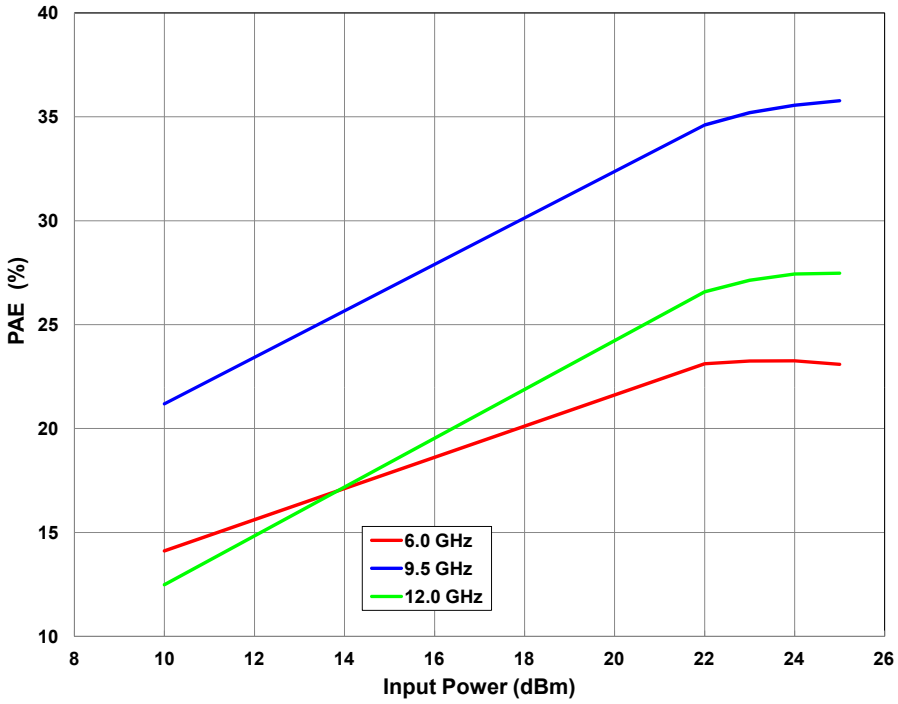

Figure 4. - Output Power vs. Input Power
V_{DD} = 28 V, I_{DQ} = 2.0 A

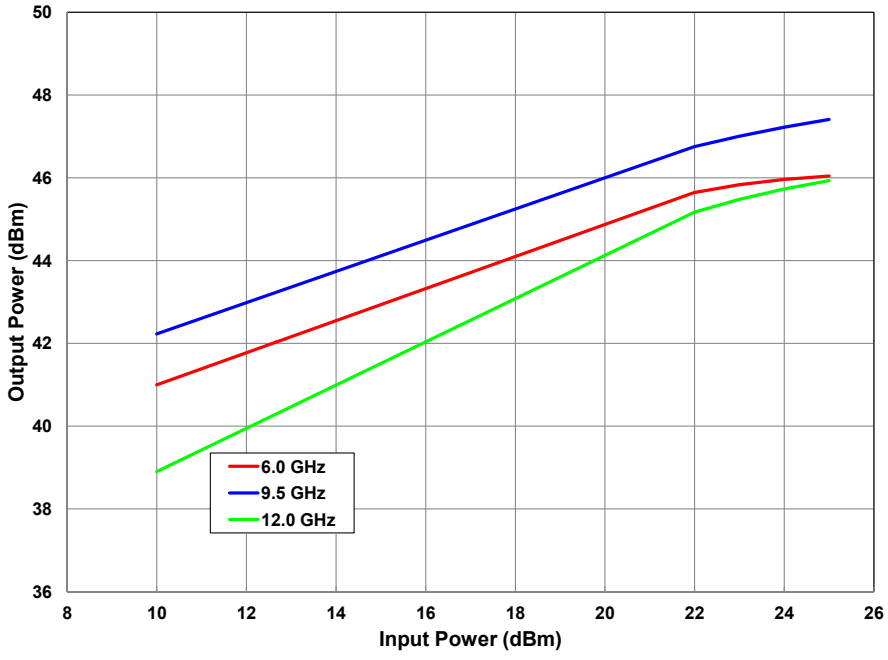

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Figure 5. - Gain vs Input Power
V_{DD} = 28 V, I_{DQ} = 2.0 A

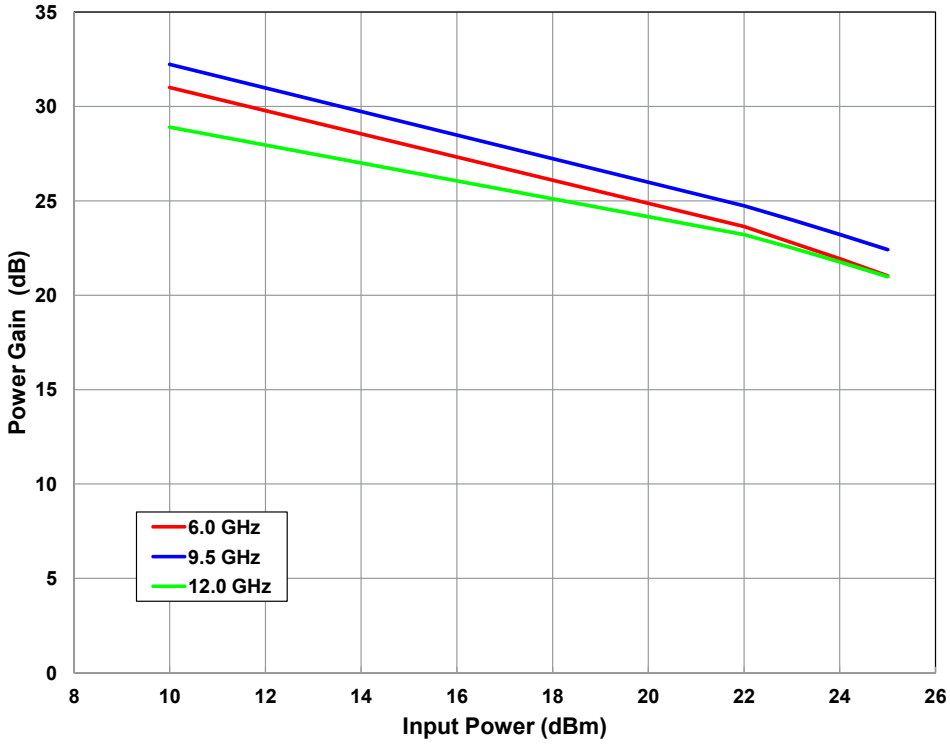
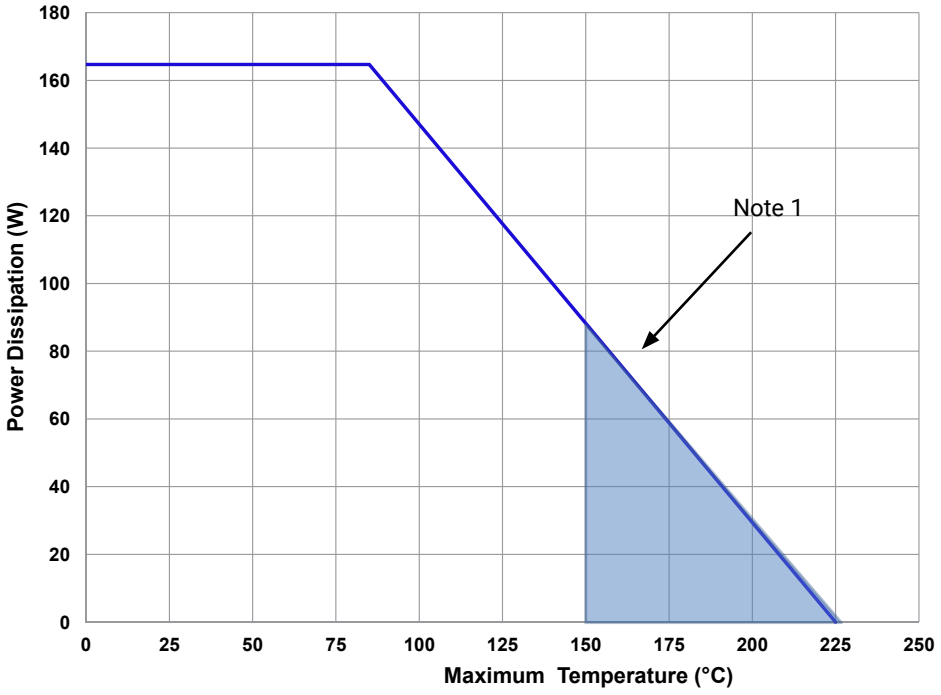


Figure 6. - Power Dissipation Derating Curve



Note 1. Area exceeds Maximum Case Operating Temperature (See Page 2).

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CMPA601C025F-AMP Demonstration Amplifier Circuit Bill of Materials

Designator	Description	Qty
C2,C4,C5,C7,C9,C12	CAP,33000PF, 0805,100V, X7R	6
C1,C3,C6,C8,C10,C13	CAP, 1.0UF, 100V, 10%, X7R, 1210	6
C11,C14	CAP ELECT 3.3UF 80V FK SMD	2
R1,R2	RES 0.0 OHM 1/16W 0402 SMD	2
J1,J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST, 20MIL	2
J3	HEADER RT>PLZ .1CEN LK 9POS	1
W1	WIRE, BLACK, 22 AWG ~ 1.50”	1
W2	WIRE, BLACK, 22 AWG ~ 1.75”	1
Q1	CMPA601C025F	1

CMPA601C025F-AMP Demonstration Amplifier Circuit

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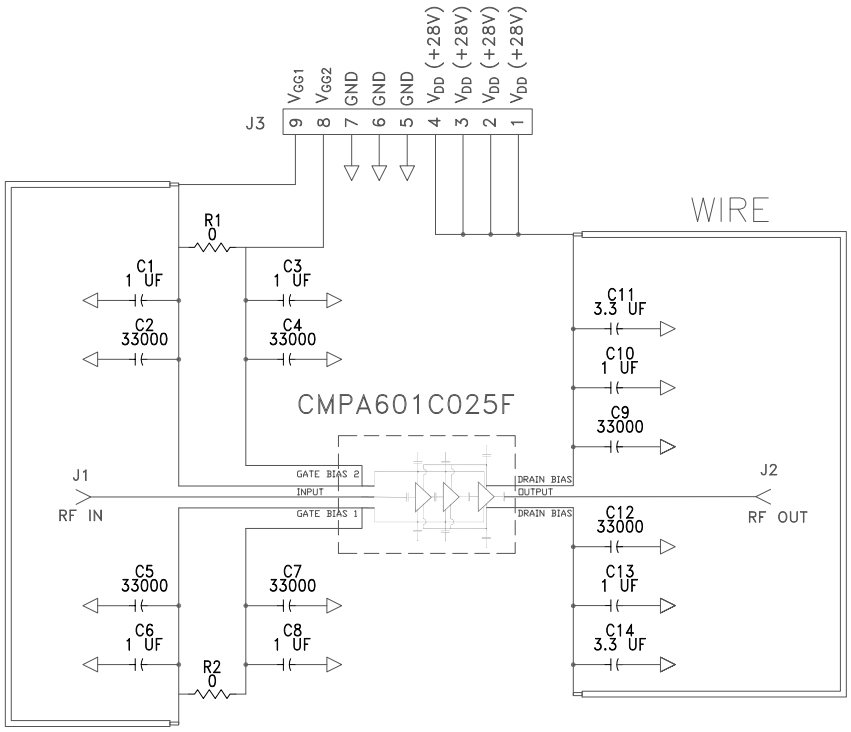
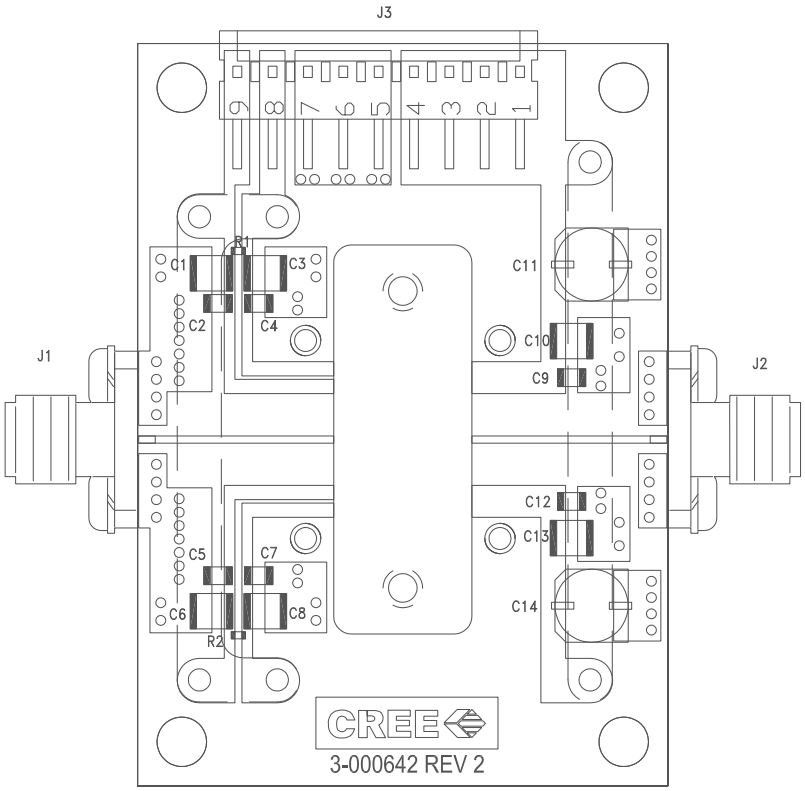
CMP601C025F-AMP Demonstration Amplifier Circuit Schematic



CMPA601C025F-AMP Demonstration Amplifier Circuit Outline



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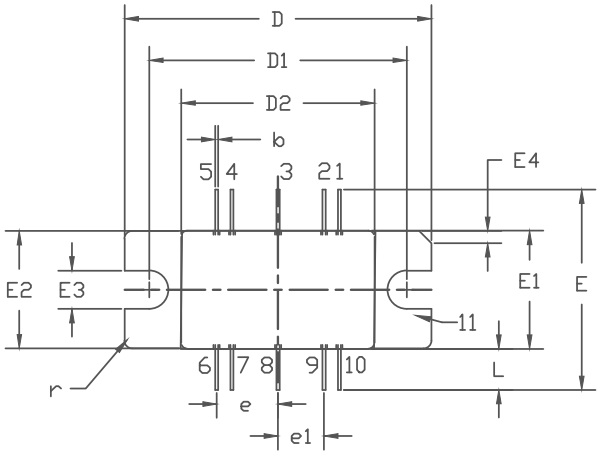
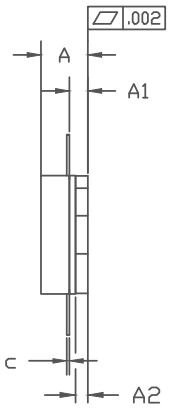
Product Dimensions CMPA601C025F





NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1994.

2. CONTROLLING DIMENSION: INCH.

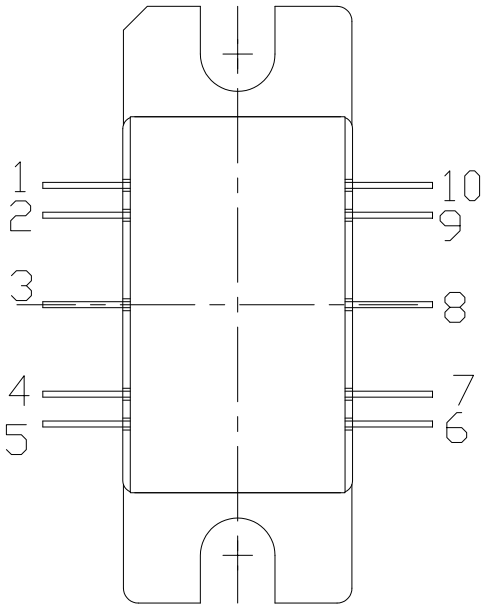
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.

4. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.

	INCHES		MILLIMETERS		NOTES
DIM	MIN	MAX	MIN	MAX	
A	0.148	0.168	3.76	4.27	
A1	0.055	0.065	1.40	1.65	
A2	0.035	0.045	0.89	1.14	
b	0.01 TYP		0.254 TYP		10x
c	0.007	0.009	0.18	0.23	
D	0.995	1.005	25.27	25.53	
D1	0.835	0.845	21.21	21.46	
D2	0.623	0.637	15.82	16.18	
E	0.653 TYP		16.59 TYP		
E1	0.380	0.390	9.65	9.91	
E2	0.380	0.390	9.65	9.91	
E3	0.120	0.130	3.05	3.30	
E4	0.035	0.045	0.89	1.14	45° CHAMFER
e	0.200 TYP		5.08 TYP		4x
e1	0.150 TYP		3.81 TYP		4x
L	0.115	0.155	2.92	3.94	10x
r	0.025 TYP		.635 TYP		3x

PIN 1: GATE BIAS 6: DRAIN BIAS
2: GATE BIAS 7: DRAIN BIAS
3: RF IN 8: RF OUT
4: GATE BIAS 9: DRAIN BIAS
5: GATE BIAS 10: DRAIN BIAS
11: SOURCE

Pin Number	Qty
1	Gate Bias for Stage 1, 2 & 3
2	Gate Bias for Stage 1, 2 & 3
3	RF IN
4	Gate Bias for Stage 1, 2 & 3
5	Gate Bias for Stage 1, 2 & 3
6	Drain Bias
7	Drain Bias
8	RF OUT
9	Drain Bias
10	Drain Bias



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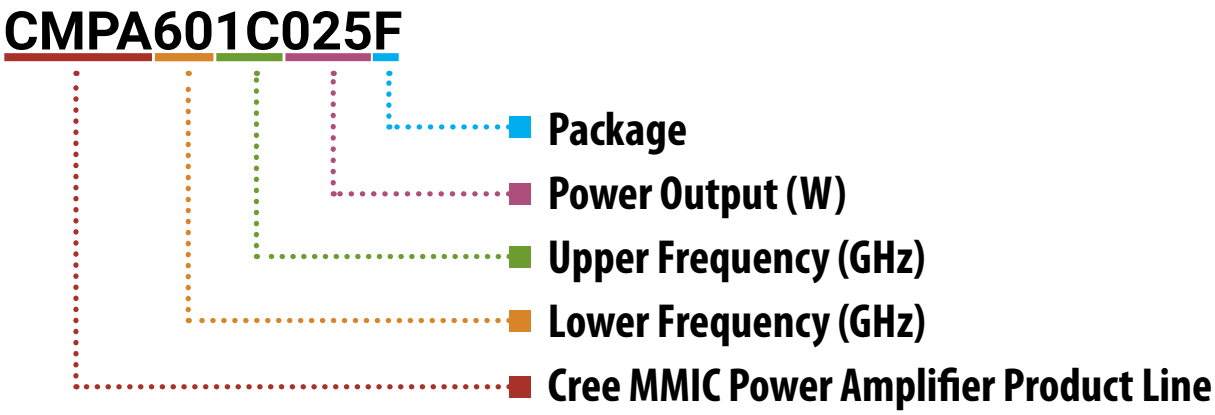
Part Number System



Parameter	Value	Units
Lower Frequency	6.0	GHz
Upper Frequency[1]	12.0	GHz
Power Output	25	W
Package	Flanged	-

Table 1.

Note[1]: Alpha characters used in frequency code indicate a value greater than 9.9 GHz. See Table 2 for value.

Character Code	Code Value
A	0
B	1
C	2
D	3
E	4
F	5
G	6
H	7
J	8
K	9
Examples:	1A = 10.0 GHz 2H = 27.0 GHz

Table 2.

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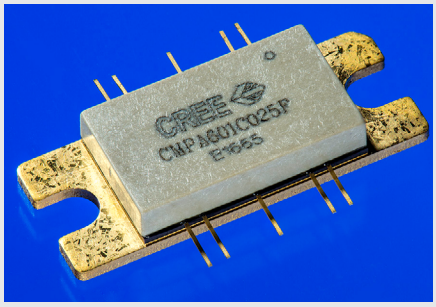
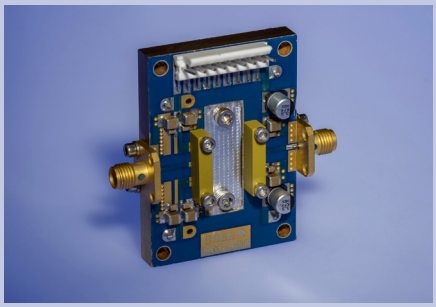
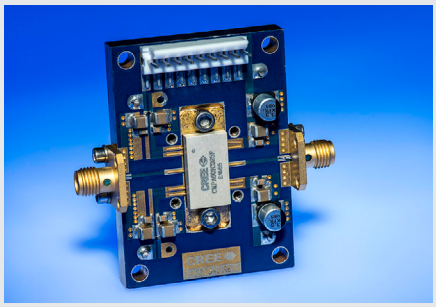
Product Ordering Information

Order Number	Description	Unit of Measure	Image
CMPA601C025F	GaN HEMT	Each	
CMPA601C025F-TB	Test board without GaN HEMT	Each	
CMPA601C025F-AMP	Test board with GaN HEMT installed	Each	

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